
2SK3001

GaAs HEMT
Low Noise Amplifier

HITACHI

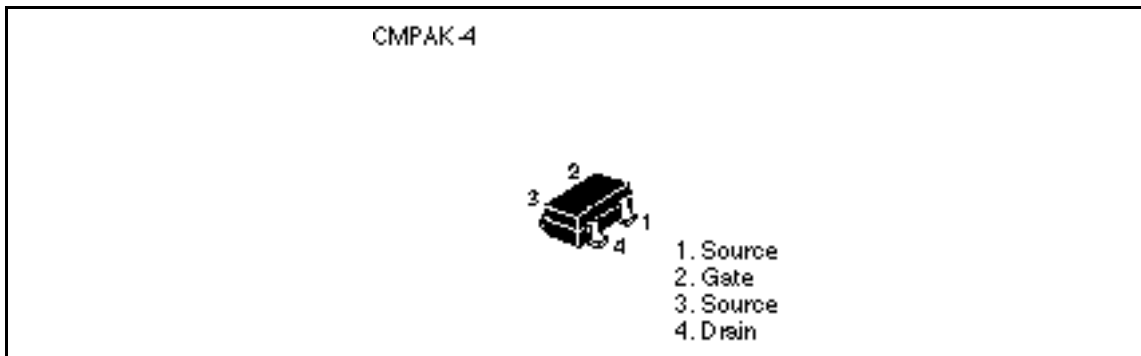
ADE-208-597(Z)
1st. Edition
December 1997

www.DataSheet4U.com

Features

- Excellent low noise characteristics.
Fmin = 0.8 dB typ. (3 V, 5 mA, 0.9 GHz)
- High associated gain.
Ga = 18 dB typ. (3 V, 5 mA, 0.9 GHz)
- Small package. (CMPAK-4)

Outline



This document may, wholly or partially, be subject to change without notice.

This Device is sensitive to Electro Static Discharge.
It is recommended to adopt appropriate cautions when handling this transistor.

CAUTION

This product use GaAs. Since dust or fume of GaAs is highly poisonous to human body, please do not treat them mechanically in the manner which might expose to the Air. And it should never be thrown out with general industrial or domestic wastes.

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Absolute Maximum Ratings (Ta = 25°C)

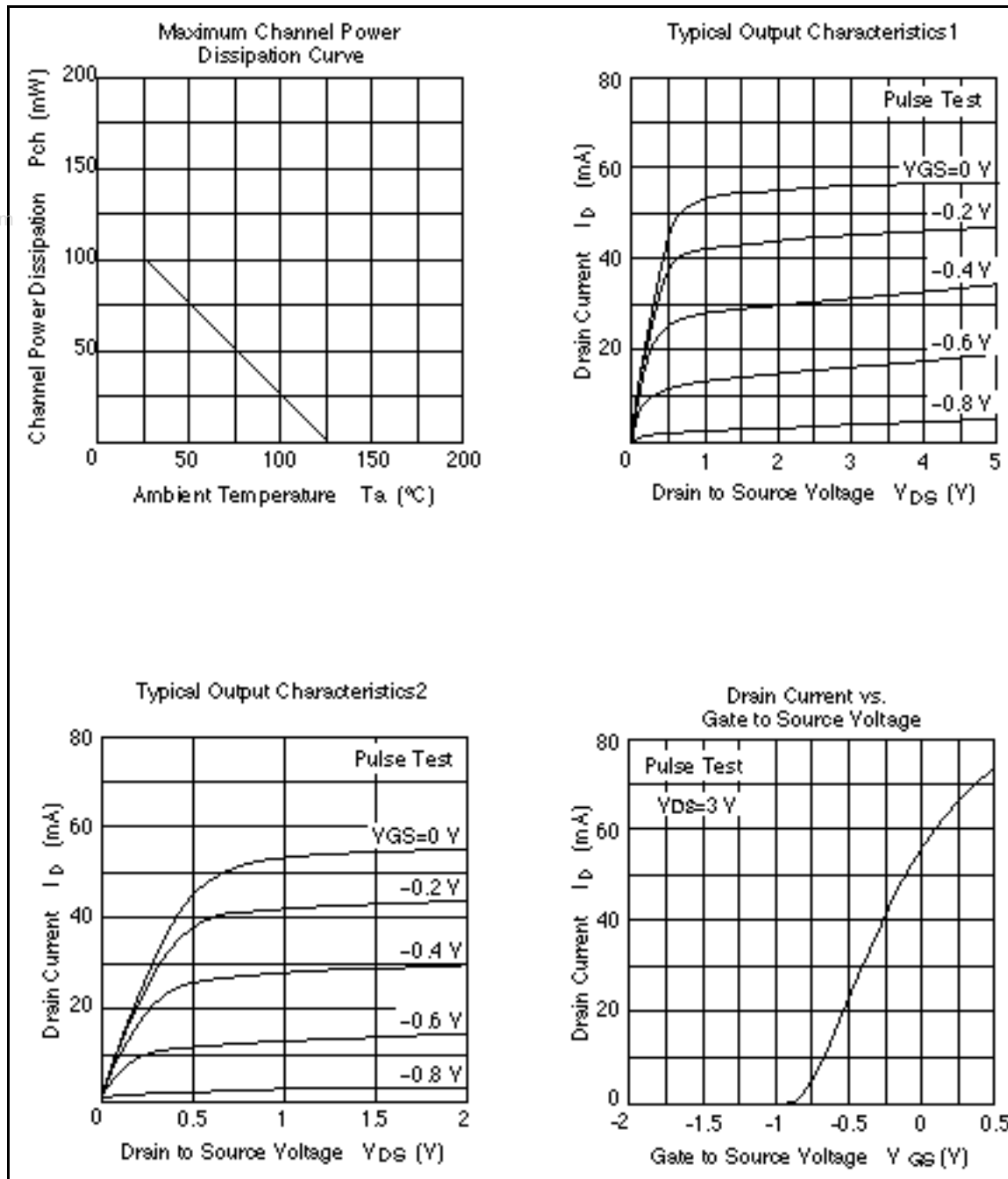
Item	Symbol	Ratings	Unit
Drain to source voltage	V _{DSS}	6	V
Gate to source voltage	V _{GSO}	-4	V
Gate to drain voltage	V _{GDO}	-4	V
Drain current	I _D	20	mA
Channel dissipation	P _{ch}	100	mW
Channel temperature	T _{ch}	125	°C
Storage temperature	T _{stg}	-55 to +125	°C

Electrical Characteristics (Ta = 25°C)

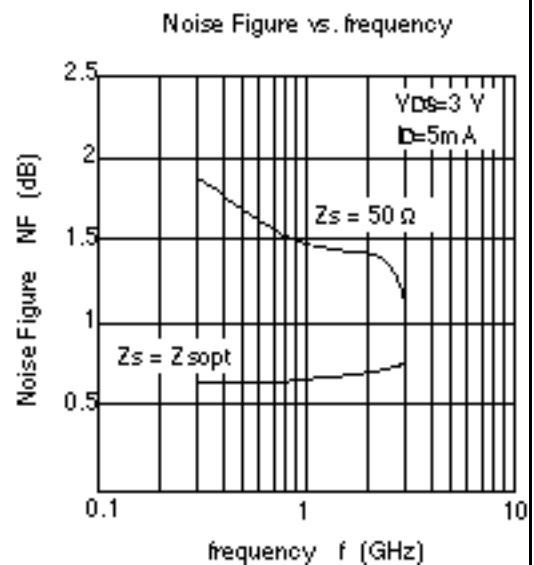
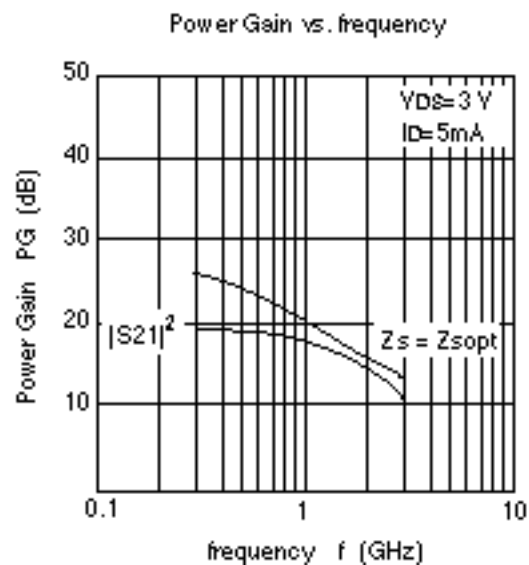
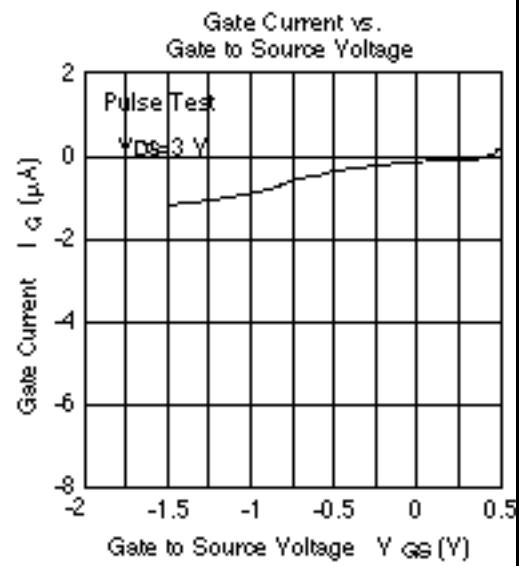
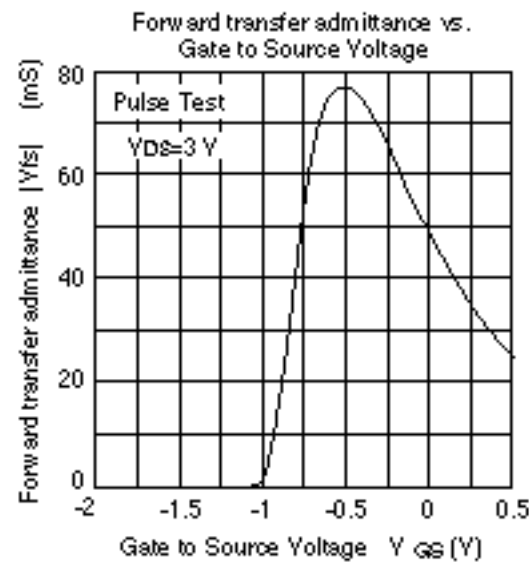
Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Gate to source leak current	I _{GSS}	—	—	-20	μA	V _{GS} = -4 V, V _{DS} = 0
Gate to source cutoff voltage	V _{GS(off)}	-0.5	—	-1.5	V	V _{DS} = 3 V, I _D = 100 μA
Drain to source current	I _{DSS}	35	50	70	mA	V _{DS} = 3 V, V _{GS} = 0 Pulse test
Forward transfer admittance	y _{fs}	40	60	—	mS	V _{DS} = 3 V, I _D = 10 mA f = 1 kHz
Power Gain	PG	15.0	18.0	—	dB	V _{DS} = 3 V, I _D = 5 mA f = 0.9 GHz
Noise Figure	NF	—	0.8	1.2	dB	
Associated gain	G _a	—	21.0	—	dB	V _{DS} = 3 V, I _D = 5 mA f = 0.8 GHz, Z _s = Z _{sopt}
Minimum noise figure	F _{min}	—	0.7	—	dB	
Associated gain	G _a	—	16.0	—	dB	V _{DS} = 3 V, I _D = 5 mA f = 1.8 GHz, Z _s = Z _{sopt}
Minimum noise figure	F _{min}	—	0.75	—	dB	

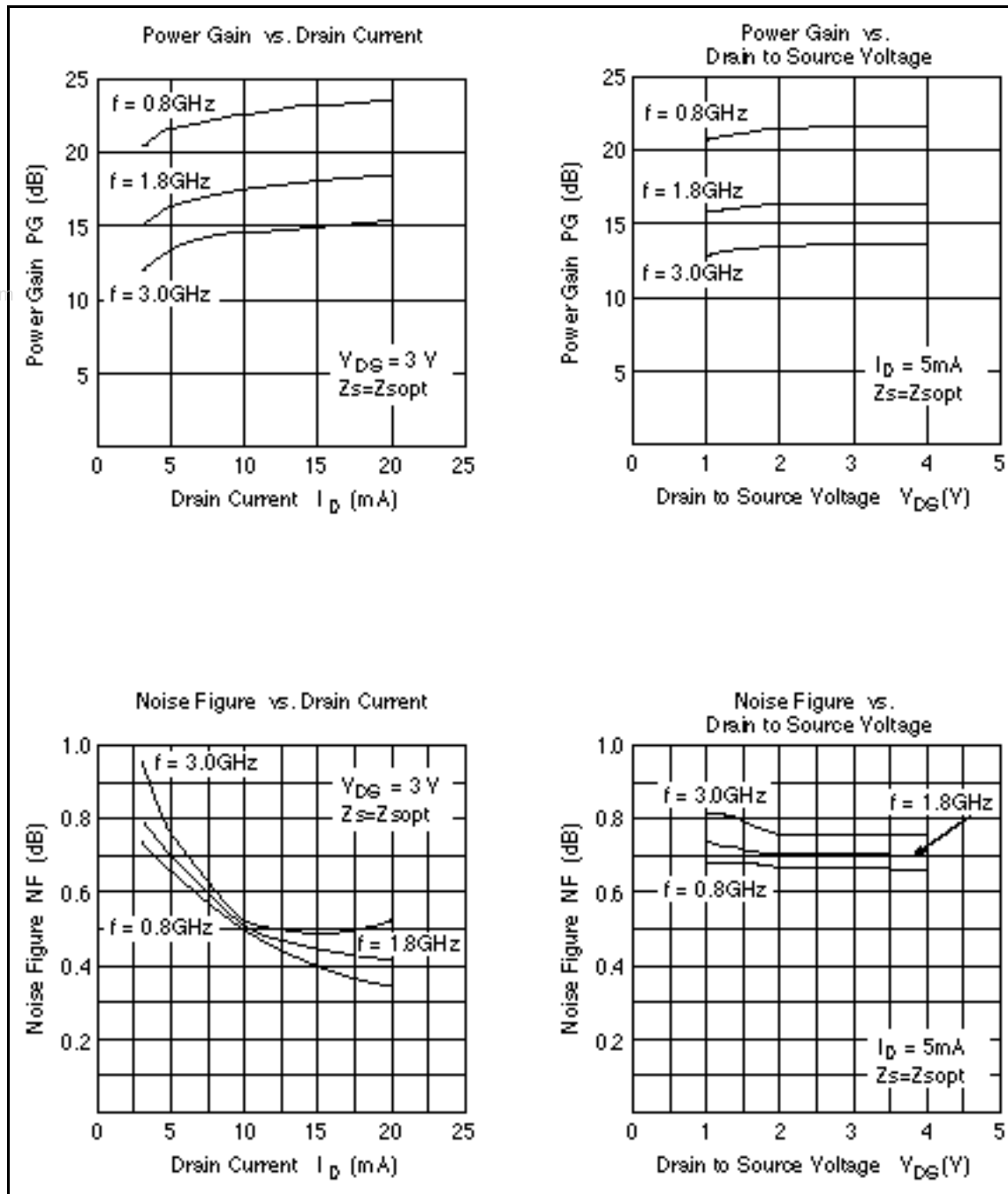
Note: Marking of 2SK3001 is "YX—"

Main Characteristics



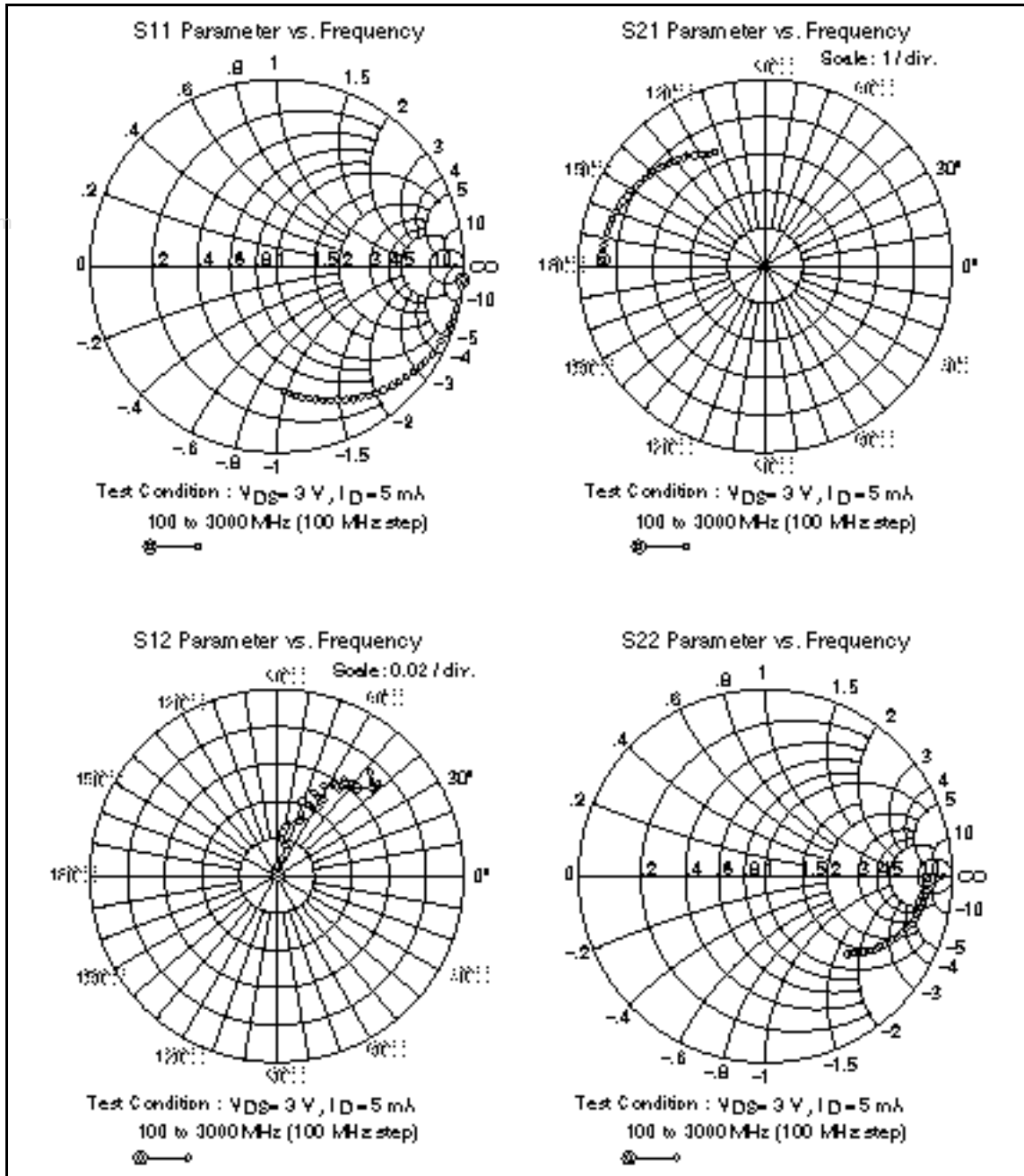
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Sparameter (Smith Plot $Z_0=50\Omega$)

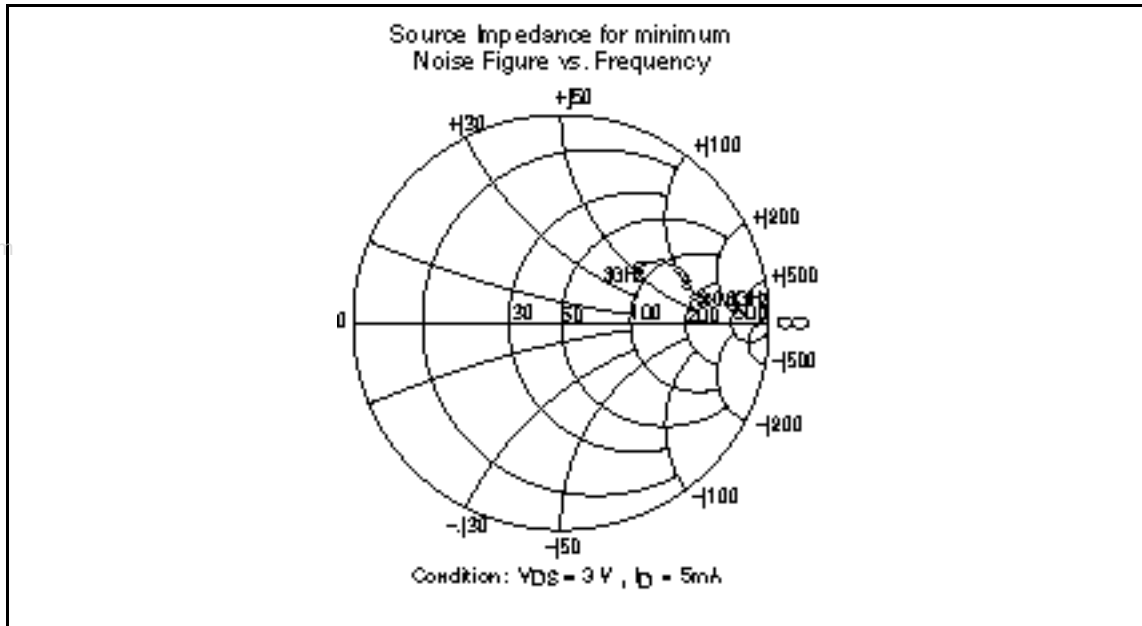


Sparameter ($V_{DS} = 3 \text{ V}$, $I_D = 5 \text{ mA}$, $Z_0 = 50 \text{ } \Omega$)

Freq (GHz)	S11 (Mag)	S11 (Ang)	S21 (Mag)	S21 (Ang)	S12 (Mag)	S12 (Ang)	S22 (Mag)	S22 (Ang)
0.1	0.998	-4.1	4.4	177.6	0.001	49.2	0.875	-1.2
0.2	0.995	-6.5	4.4	175.1	0.005	86.3	0.869	-3.1
0.3	0.993	-10.9	4.4	172.6	0.010	75.2	0.869	-5.1
0.4	0.990	-13.4	4.3	170.2	0.017	73.6	0.863	-6.7
0.5	0.989	-14.5	4.3	169.1	0.015	82.9	0.865	-7.1
0.6	0.981	-17.0	4.3	166.3	0.020	81.6	0.859	-9.0
0.7	0.976	-20.0	4.3	163.9	0.026	73.7	0.856	-10.6
0.8	0.965	-23.5	4.3	161.4	0.025	74.3	0.851	-12.1
0.9	0.956	-28.2	4.2	159.0	0.032	76.5	0.834	-14.0
1.0	0.949	-31.1	4.2	156.4	0.029	75.2	0.837	-15.4
1.1	0.942	-33.9	4.2	154.3	0.036	65.0	0.830	-16.8
1.2	0.930	-36.3	4.1	152.0	0.039	67.0	0.819	-18.4
1.3	0.918	-39.5	4.1	149.6	0.037	65.4	0.810	-20.1
1.4	0.903	-42.2	4.0	147.4	0.042	61.2	0.800	-21.8
1.5	0.895	-44.8	4.0	145.1	0.045	65.9	0.789	-23.1
1.6	0.882	-47.8	3.9	143.1	0.046	60.5	0.779	-24.4
1.7	0.869	-50.9	4.0	140.7	0.053	61.8	0.768	-26.0
1.8	0.856	-53.3	3.9	138.3	0.056	57.4	0.753	-27.2
1.9	0.843	-55.6	3.8	136.7	0.055	56.8	0.747	-28.7
2.0	0.826	-59.0	3.9	133.9	0.059	53.8	0.736	-30.4
2.1	0.814	-61.8	3.8	132.3	0.059	52.9	0.720	-31.5
2.2	0.800	-64.0	3.7	130.0	0.062	48.2	0.710	-32.6
2.3	0.785	-67.0	3.7	128.1	0.059	51.5	0.700	-34.4
2.4	0.767	-69.8	3.6	126.8	0.063	48.5	0.692	-35.4
2.5	0.751	-72.4	3.6	123.5	0.065	47.6	0.676	-36.7
2.6	0.742	-75.0	3.5	123.3	0.065	47.4	0.661	-37.9
2.7	0.719	-78.3	3.5	120.0	0.063	48.7	0.652	-39.2
2.8	0.710	-80.3	3.4	118.9	0.074	46.7	0.645	-40.0
2.9	0.689	-82.8	3.3	116.9	0.070	41.0	0.630	-41.4
3.0	0.675	-85.6	3.4	116.0	0.074	41.8	0.618	-43.7

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optimize ($V_{DS} = 3\text{ V}$, $I_D = 5\text{ mA}$)

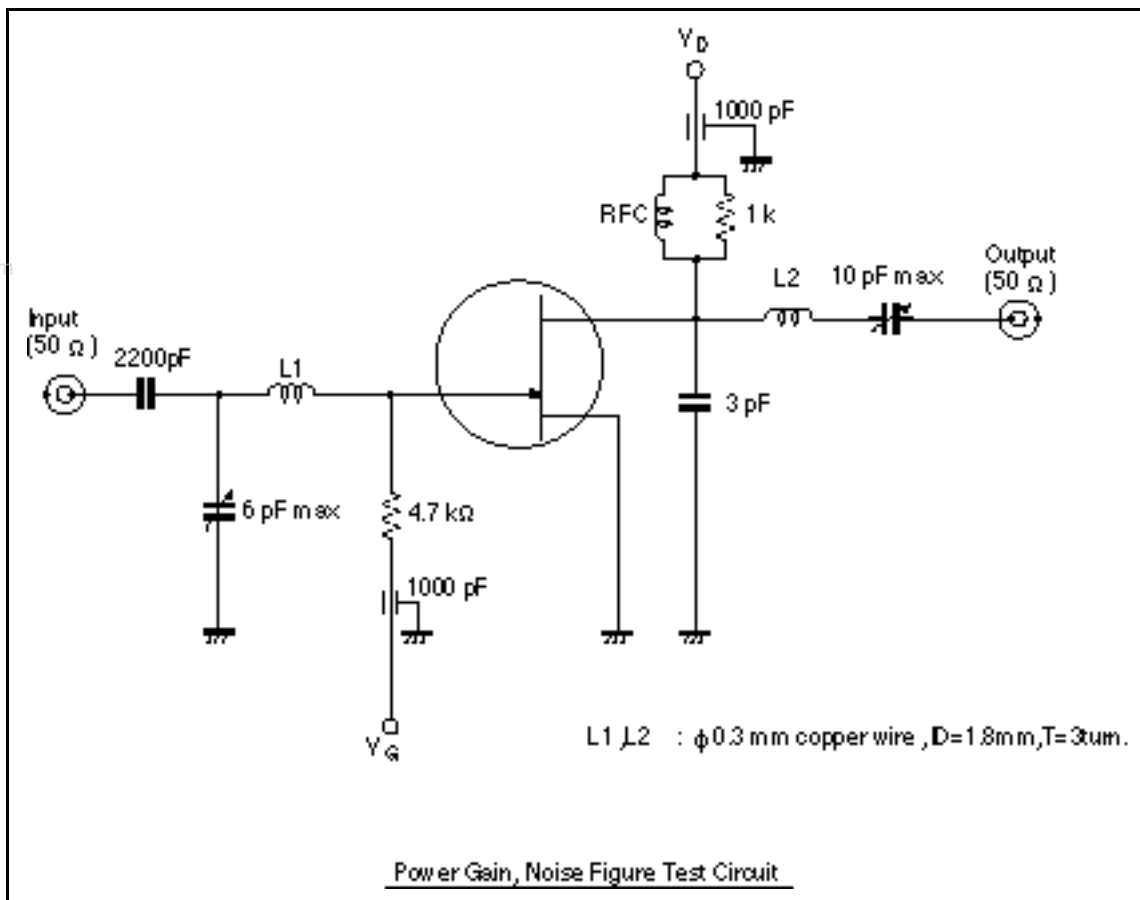


Noise parameter ($V_{DS} = 3\text{ V}$, $I_D = 5\text{ mA}$)

Freq (GHz)	Fmin ¹ (dB)	Ga (dB)	Gopt (Mag)	Gopt (Ang)	RN ()	NF 50 ² (dB)	S21 ² (dB)	S21 ² -
0.8	0.67	21.7	0.69	8.8	19.1	1.53	18.2	4.26
0.9	0.67	21.0	0.68	9.8	18.7	1.50	18.0	4.24
1.0	0.67	20.3	0.66	10.7	18.4	1.48	17.5	4.19
1.5	0.69	17.6	0.64	15.7	17.5	1.44	16.0	3.99
1.7	0.70	16.8	0.64	17.8	17.4	1.44	15.3	3.92
1.8	0.71	16.4	0.64	18.9	17.3	1.44	15.0	3.88
1.9	0.71	16.1	0.64	20.1	17.1	1.44	14.8	3.85
2.0	0.72	15.8	0.64	21.3	17.0	1.44	14.2	3.76
2.2	0.72	15.2	0.63	23.8	16.6	1.43	13.6	3.69
2.5	0.74	14.6	0.60	28.1	15.6	1.37	12.3	3.50
2.7	0.74	14.2	0.56	31.3	14.6	1.30	11.9	3.44
3.0	0.76	13.6	0.47	36.7	12.6	1.15	11.1	3.33

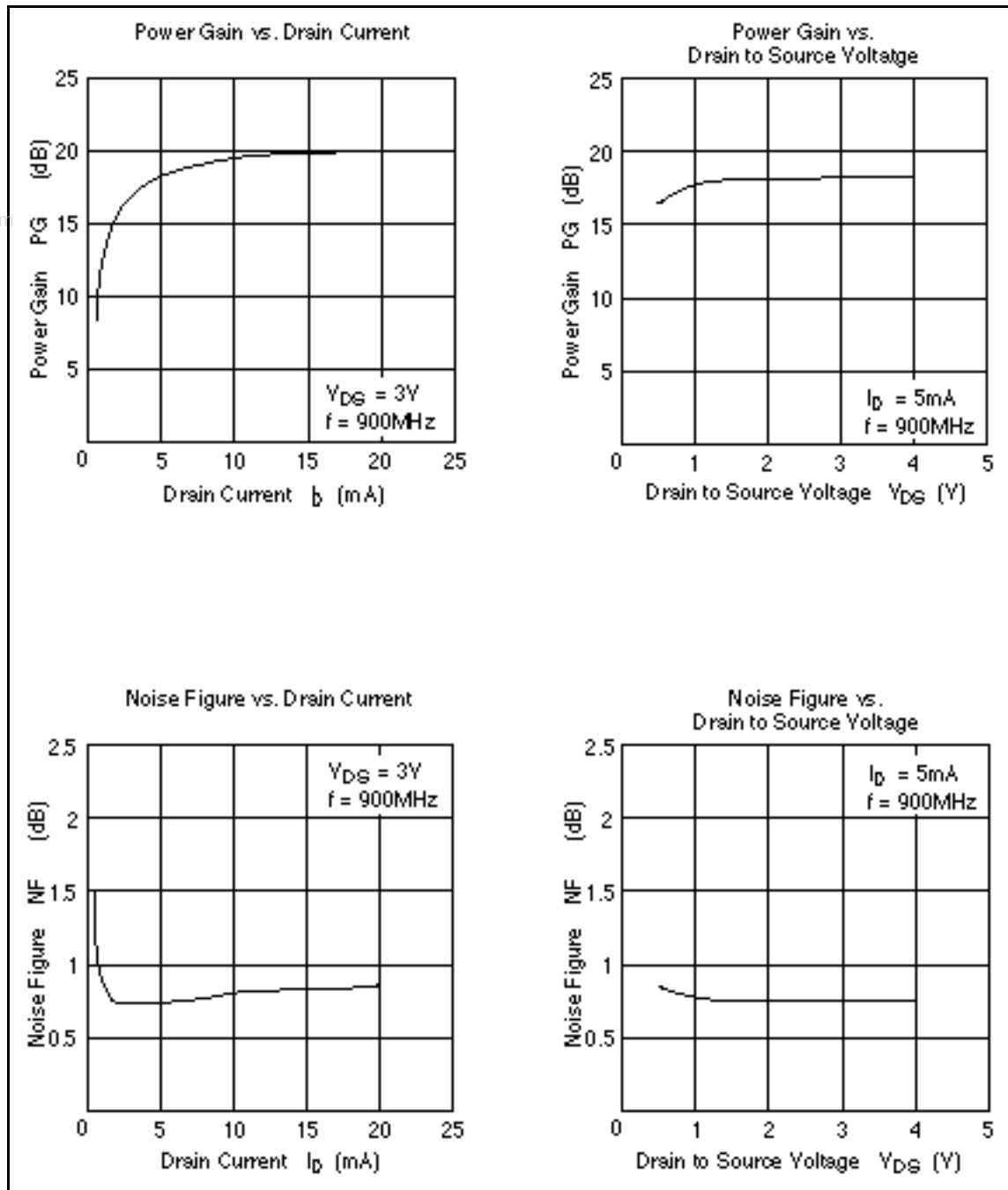
note 1. Input matched for minimum noise figure, Output for maximum gain.

2. $Z_s = Z_L = 50$

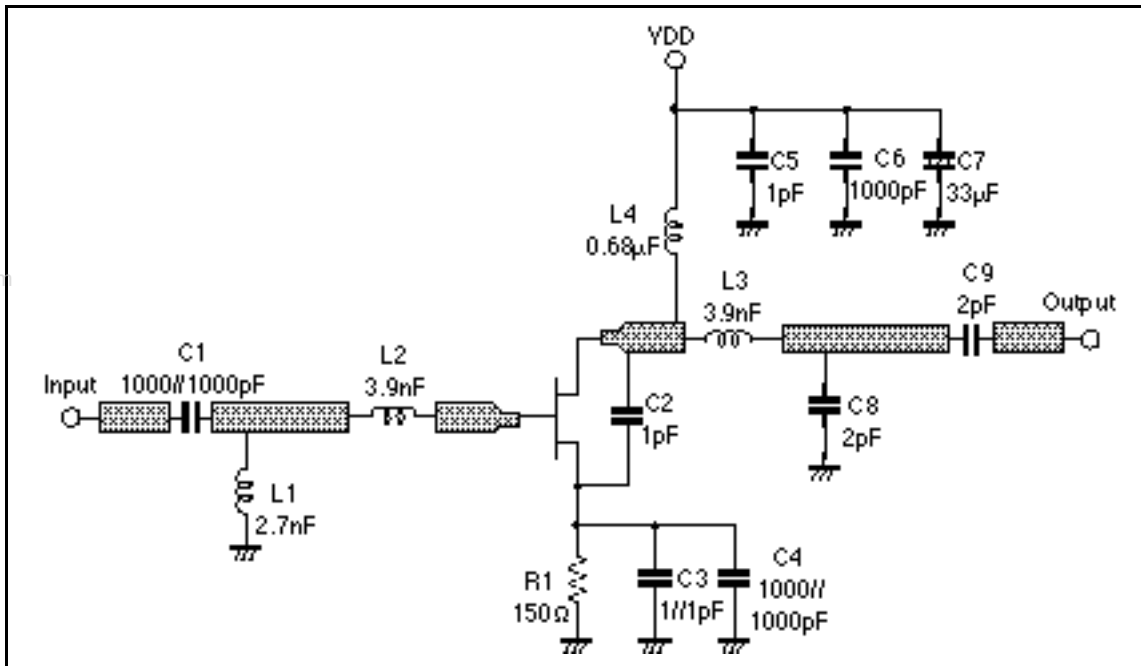
Test Fixture ($f = 0.9 \text{ GHz}$)

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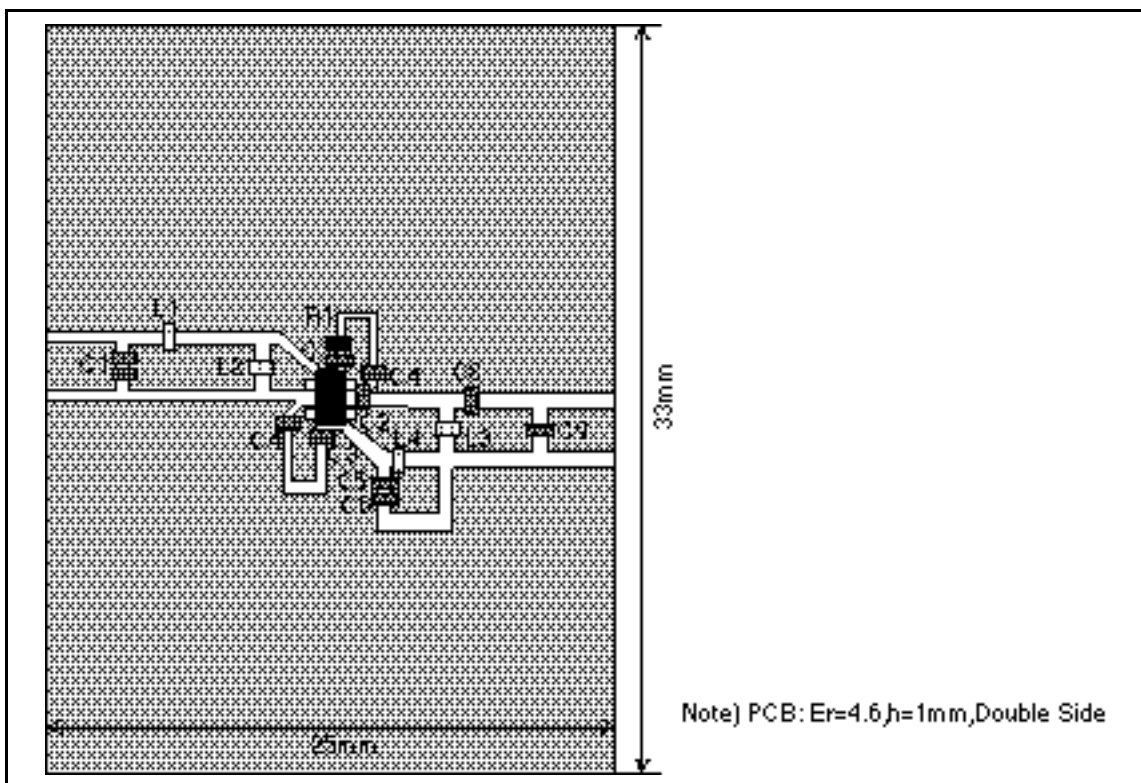
Characteristics (Test Fixture)



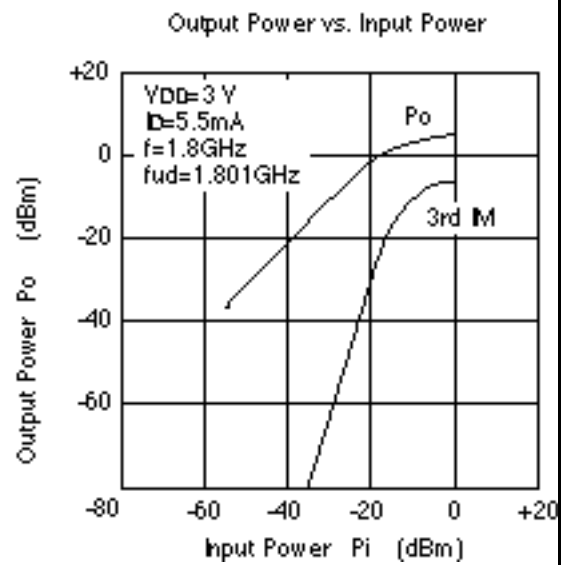
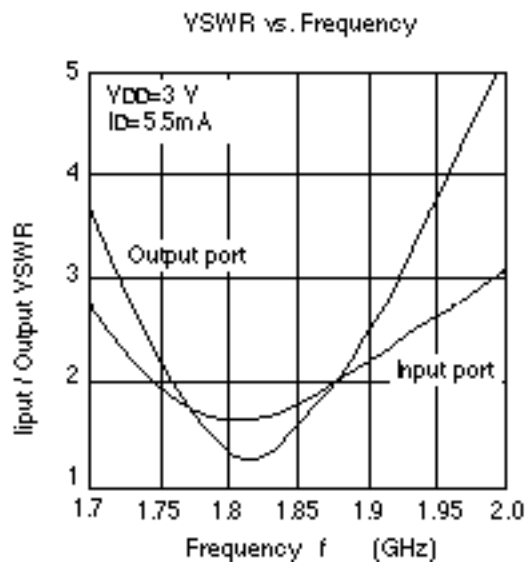
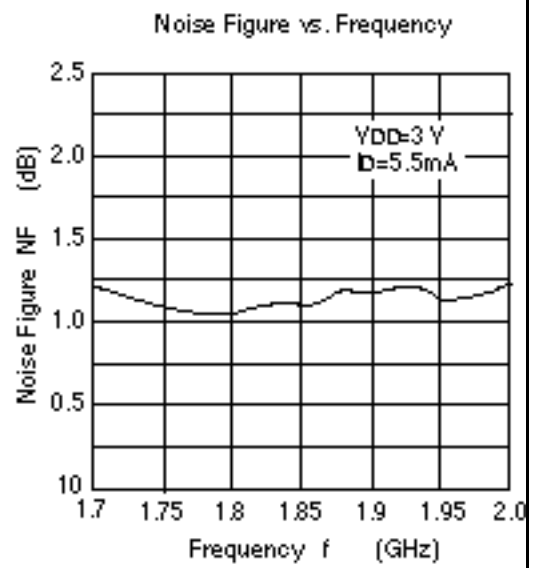
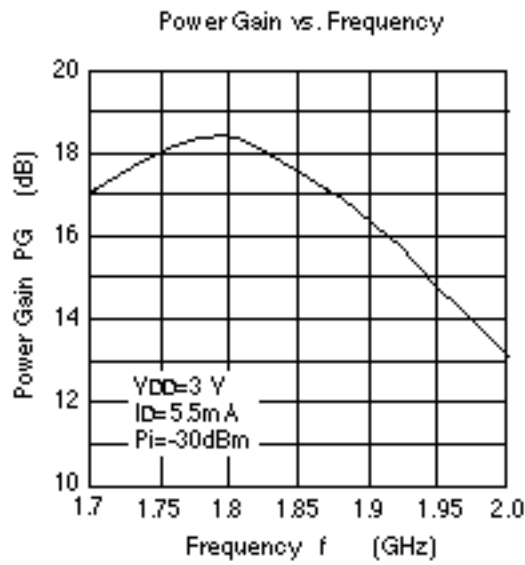
Application (f = 1.8 GHz LNA)



PCB Pattern & Parts Layouts

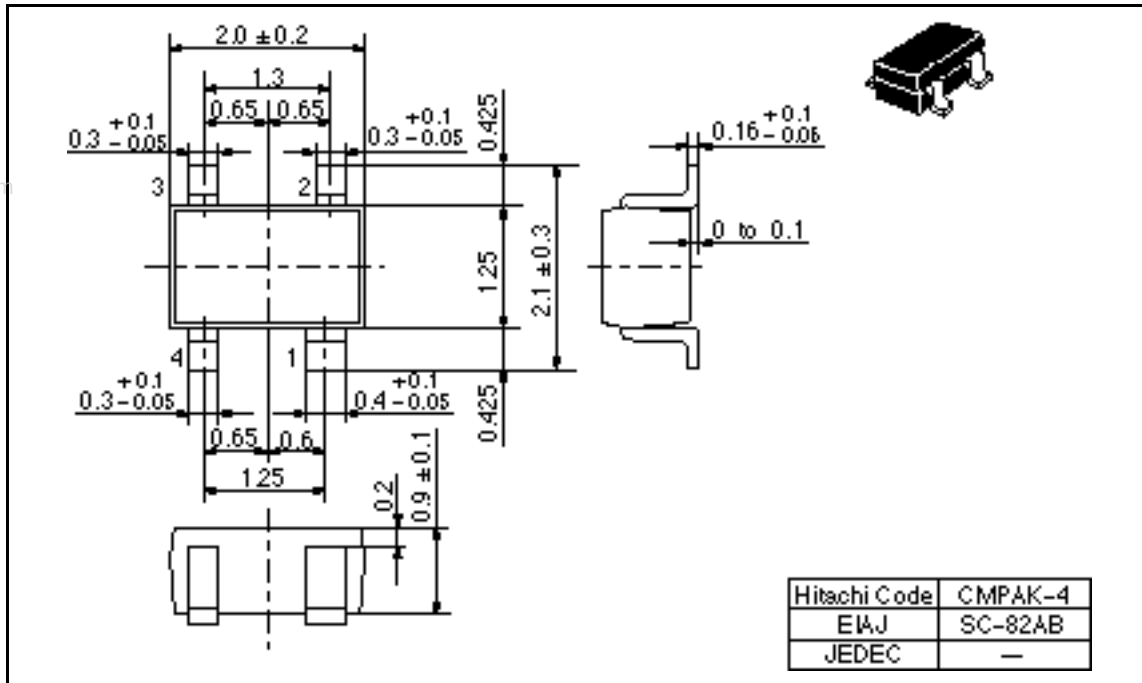


Characteristics



Package Dimensions

Unit: mm



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